

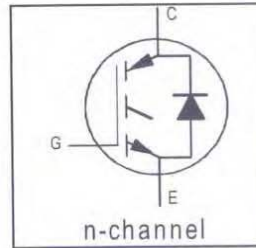
IRG4PH20KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
 ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
 UltraFast IGBT

Features

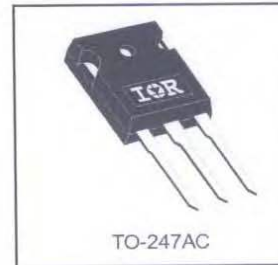
- High short circuit rating optimized for motor control, $t_{sc} = 10\mu s$, $V_{CC} = 720V$, $T_J = 125^\circ C$, $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- Tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes



$V_{CES} = 1200V$
 $V_{CE(on) typ.} = 3.17V$
 @ $V_{GE} = 15V, I_C = 5.0A$

Benefits

- Latest generation 4 IGBT's offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses
- Lead-Free



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	11	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	5.0	
I_{CM}	Pulsed Collector Current ①	22	
I_{LM}	Clamped Inductive Load Current ②	22	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	5.0	
I_{FM}	Diode Maximum Forward Current	22	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf·in (1.1 N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	2.1	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	3.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage ^③	1200	—	—	V	V _{GE} = 0V, I _C = 250μA
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	1.13	—	V/°C	V _{GE} = 0V, I _C = 2.5mA
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	3.17	4.3	V	I _C = 5.0A V _{GE} = 15V
		—	4.04	—		I _C = 11A See Fig. 2, 5
		—	2.84	—		I _C = 5.0A, T _J = 150°C
V _{GE(th)}	Gate Threshold Voltage	3.5	—	6.5		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	V _{CE} = V _{GE} , I _C = 1mA
g _{fe}	Forward Transconductance ^④	2.3	3.5	—	S	V _{CE} = 100V, I _C = 5.0A
I _{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V _{GE} = 0V, V _{CE} = 1200V
		—	—	1000		V _{GE} = 0V, V _{CE} = 1200V, T _J = 150°C
V _{FM}	Diode Forward Voltage Drop	—	2.5	2.9	V	I _C = 5.0A See Fig. 13
		—	2.2	2.6		I _C = 5.0A, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	28	43	nC	I _C = 5.0A
Q _{ge}	Gate - Emitter Charge (turn-on)	—	4.4	6.6		V _{CC} = 400V See Fig.8
Q _{gc}	Gate - Collector Charge (turn-on)	—	12	18		V _{GE} = 15V
t _{d(on)}	Turn-On Delay Time	—	50	—	ns	T _J = 25°C
t _r	Rise Time	—	30	—		I _C = 5.0A, V _{CC} = 800V
t _{d(off)}	Turn-Off Delay Time	—	100	150		V _{GE} = 15V, R _G = 50Ω
t _f	Fall Time	—	250	380		Energy losses include "tail" and diode reverse recovery
E _{on}	Turn-On Switching Loss	—	0.62	—	mJ	See Fig. 9,10,18
E _{off}	Turn-Off Switching Loss	—	0.30	—		
E _{ts}	Total Switching Loss	—	0.92	1.2		
t _{sc}	Short Circuit Withstand Time	10	—	—	μs	V _{CC} = 720V, T _J = 125°C V _{GE} = 15V, R _G = 50Ω
t _{d(on)}	Turn-On Delay Time	—	50	—	ns	T _J = 150°C, See Fig. 10,11,18
t _r	Rise Time	—	30	—		I _C = 5.0A, V _{CC} = 800V
t _{d(off)}	Turn-Off Delay Time	—	110	—		V _{GE} = 15V, R _G = 50Ω,
t _f	Fall Time	—	620	—		Energy losses include "tail" and diode reverse recovery
E _{ts}	Total Switching Loss	—	1.6	—	mJ	
L _E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C _{ies}	Input Capacitance	—	435	—	pF	V _{GE} = 0V
C _{oes}	Output Capacitance	—	44	—		V _{CC} = 30V See Fig. 7
C _{res}	Reverse Transfer Capacitance	—	8.3	—		f = 1.0MHz
t _{rr}	Diode Reverse Recovery Time	—	51	77	ns	T _J = 25°C See Fig. 14
		—	68	102		T _J = 125°C
I _{rr}	Diode Peak Reverse Recovery Current	—	6.0	9.0	A	T _J = 25°C See Fig. 15
		—	7.0	11		T _J = 125°C
Q _{rr}	Diode Reverse Recovery Charge	—	183	274	nC	T _J = 25°C See Fig. 16
		—	285	427		T _J = 125°C
di _(rec) /dt	Diode Peak Rate of Fall of Recovery During t _b	—	380	—	A/μs	T _J = 25°C See Fig. 17
		—	307	—		T _J = 125°C

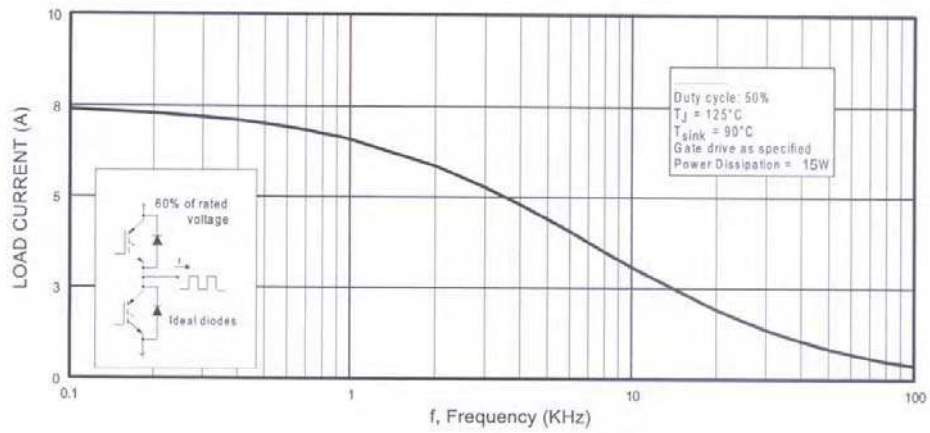


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

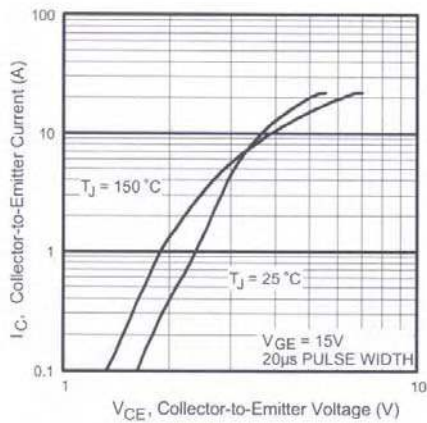


Fig. 2 - Typical Output Characteristics

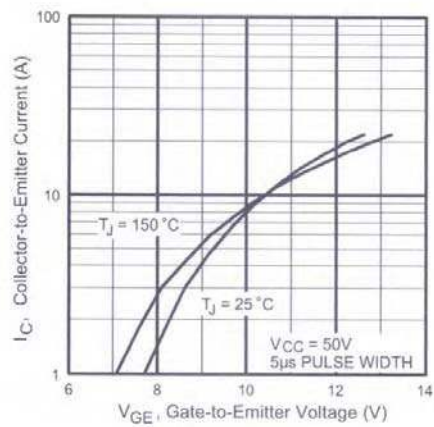


Fig. 3 - Typical Transfer Characteristics

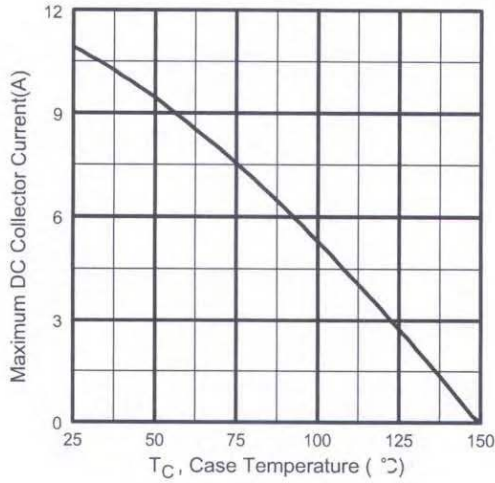


Fig. 4 - Maximum Collector Current vs. Case Temperature

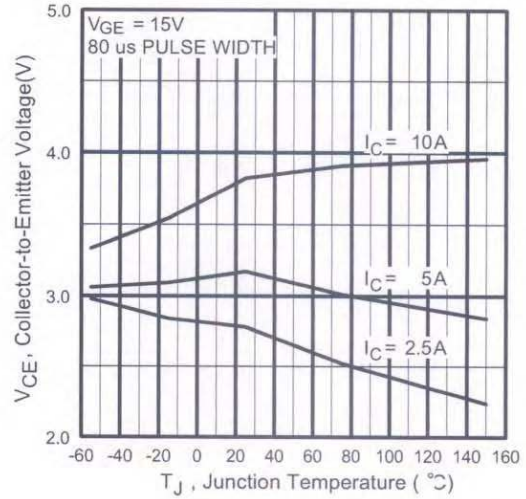


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

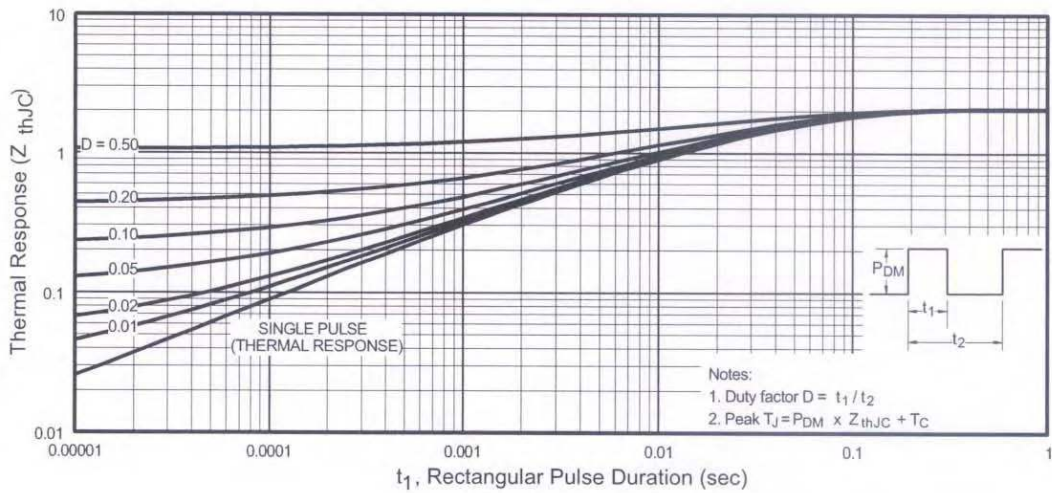


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

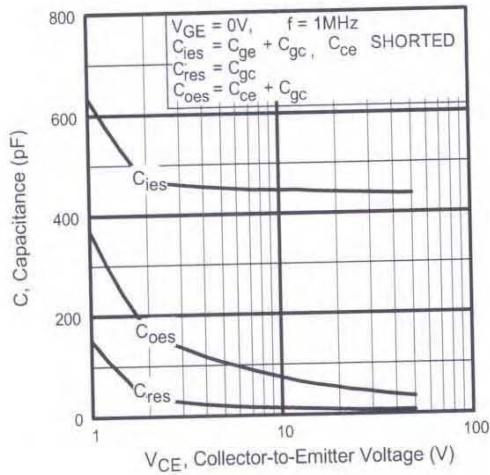


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

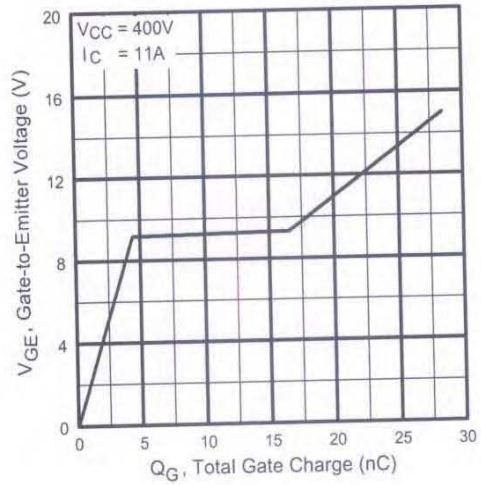


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

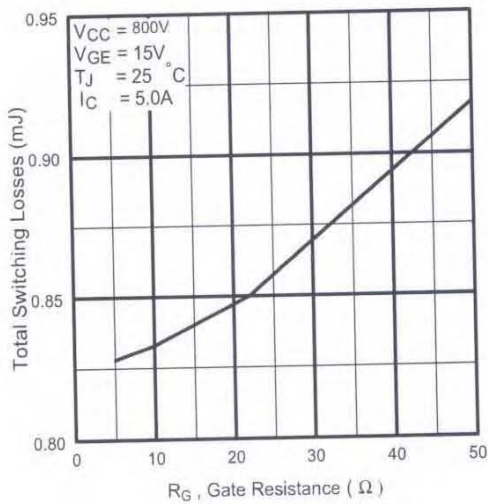


Fig. 9 - Typical Switching Losses vs. Gate Resistance

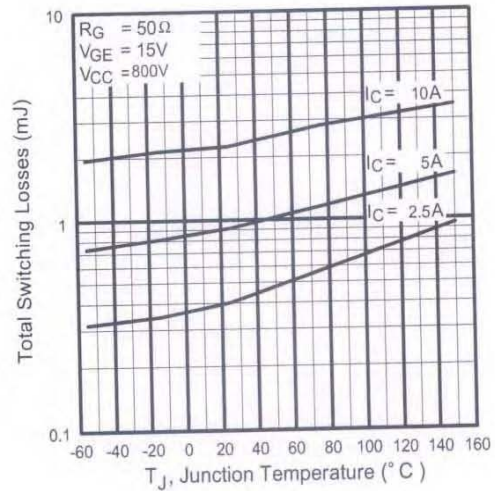


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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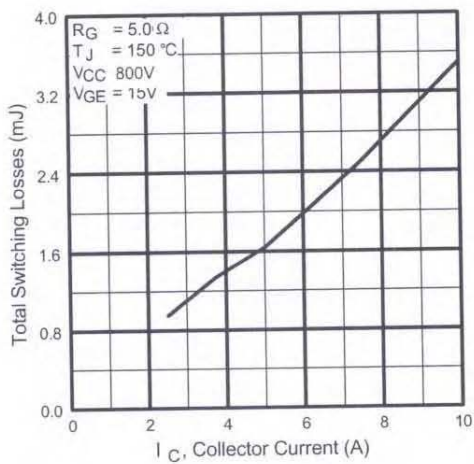


Fig. 11 - Typical Switching Losses vs. Collector Current

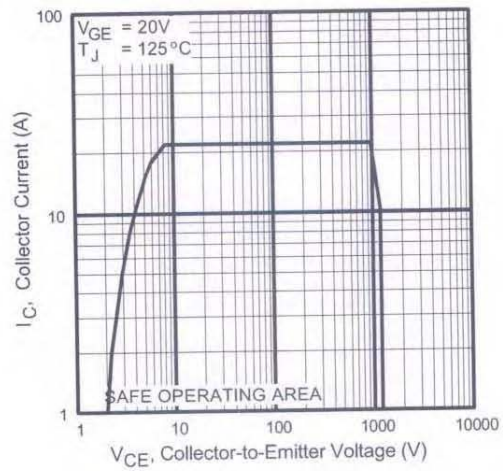


Fig. 12 - Turn-Off SOA

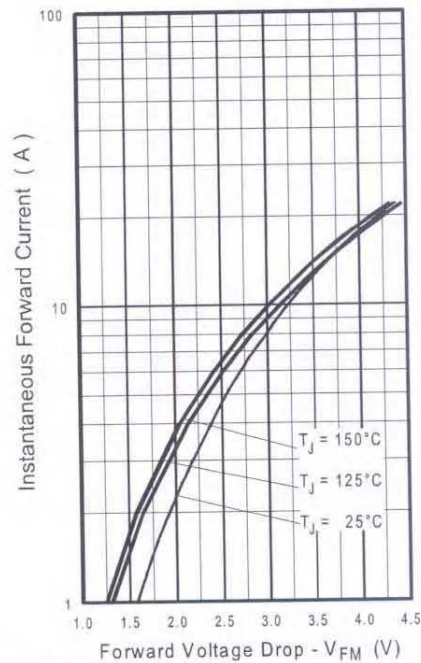


Fig. 13 - Typical Forward Voltage Drop vs. Instantaneous Forward Current

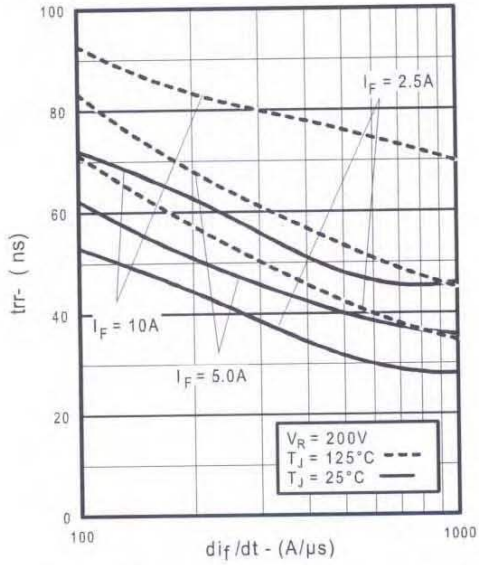


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

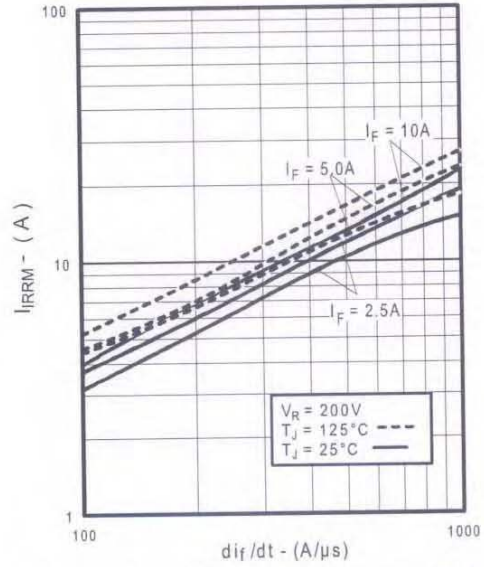


Fig. 15 - Typical Recovery Current vs. di_f/dt

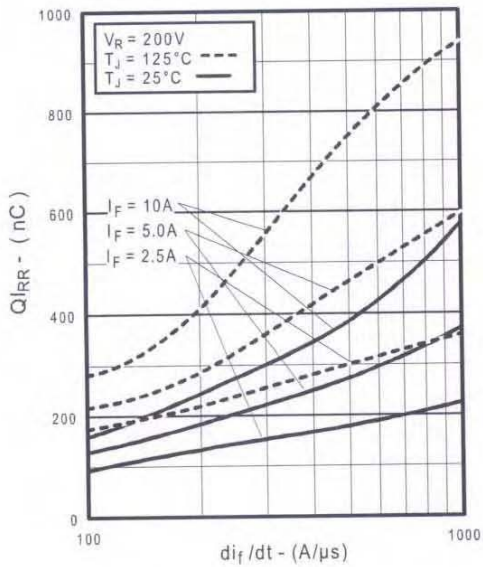


Fig. 16 - Typical Stored Charge vs. di_f/dt

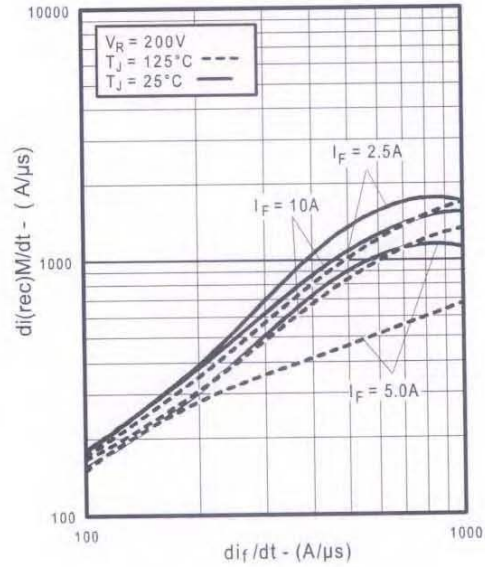


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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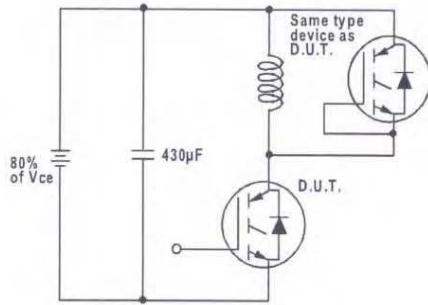


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

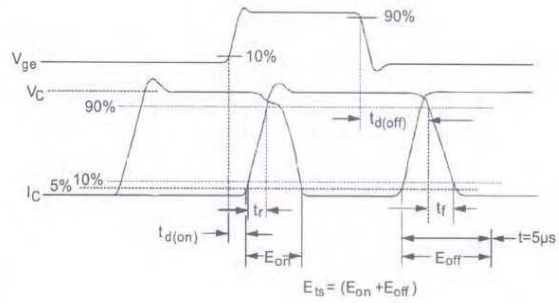


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

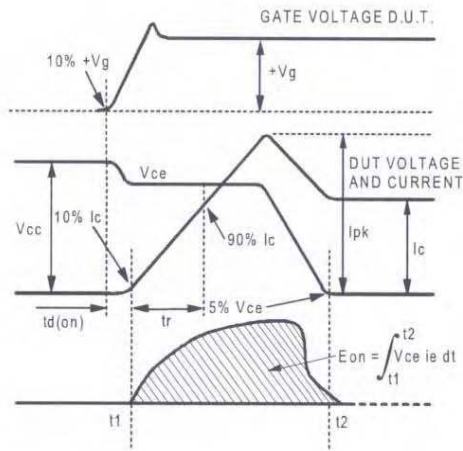


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

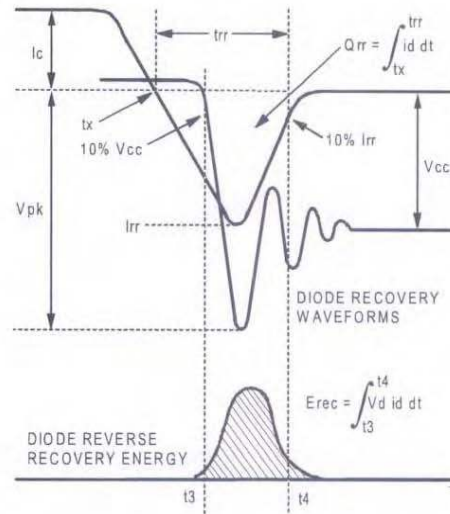


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

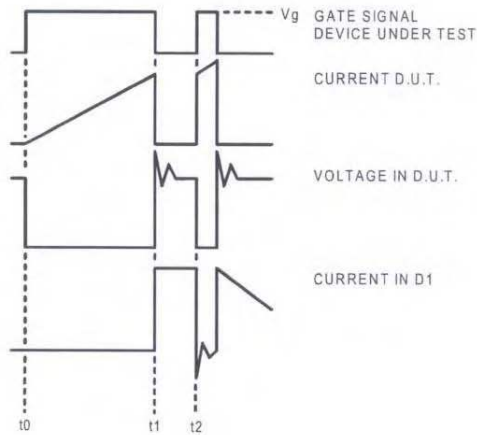


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

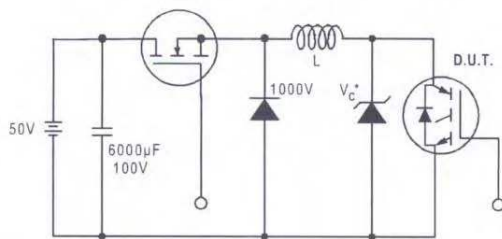


Figure 19. Clamped Inductive Load Test Circuit

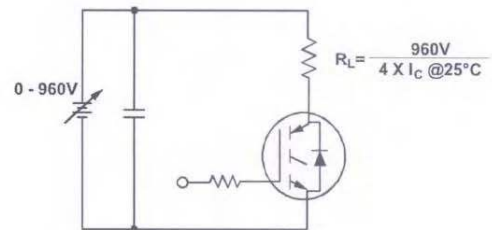


Figure 20. Pulsed Collector Current Test Circuit

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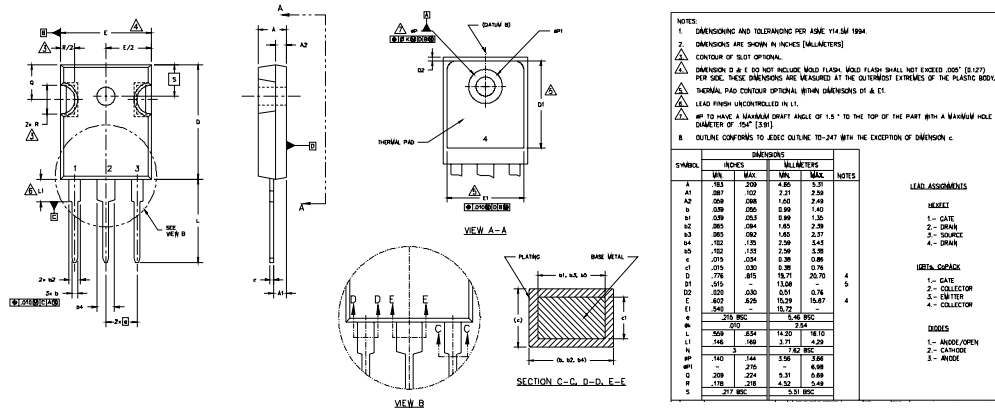
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Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=5.0\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

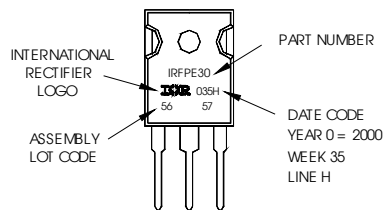
TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"
Note: "P" in assembly line
position indicates "Lead-Free"



Data and specifications subject to change without notice.

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Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>